

## N-channel Enhancement Mode Power MOSFET

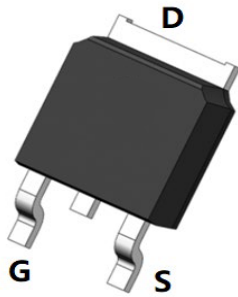
### Features

- $V_{DS} = 200\text{ V}$ ,  $I_D = 8\text{ A}$   
 $R_{DS(ON)} < 260\text{ m}\Omega$  @  $V_{GS} = 10\text{ V}$   
 $R_{DS(ON)} < 300\text{ m}\Omega$  @  $V_{GS} = 4.5\text{ V}$

### General Features

- Advanced Trench Technology
- Provide Excellent  $R_{DS(ON)}$  and Low Gate Charge
- Lead Free and Green Available

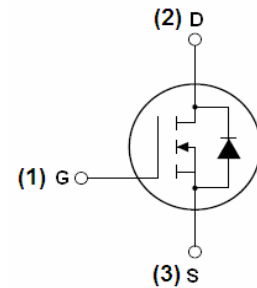
100% UIS TESTED!  
 100%  $\Delta V_{ds}$  TESTED!



TO-252-2L Top View



Pin Assignment



Schematic Diagram

### Absolute Maximum Ratings ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	200	
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Drain Current-Continuous	$I_D$	8	
Drain Current-Continuous ( $T_C = 100^\circ\text{C}$ )	$I_D(100^\circ\text{C})$	5	A
Pulsed Drain Current	$I_{DM}$	20	
Maximum Power Dissipation	$P_D$	55	
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ\text{C}$

### Thermal Characteristic

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	$R_{\theta JC}$	2.3	$^\circ\text{C}/\text{W}$
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**Electrical Characteristics ( $T_C=25^{\circ}\text{C}$  unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	200	215	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=200V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1		3.0	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=4.5A$	-	260		m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=25V, I_D=4.5A$	3	-	-	S
<b>Dynamic Characteristics</b> (Note 4)						
Input Capacitance	$C_{iss}$	$V_{DS}=25V, V_{GS}=0V,$ $F=1.0\text{MHz}$		540		PF
Output Capacitance	$C_{oss}$			90		PF
Reverse Transfer Capacitance	$C_{rss}$			35		PF
<b>Switching Characteristics</b> (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=100V, I_D=4.5A$ $V_{GS}=10V, R_{GEN}=5\Omega$	-	6.4	-	nS
Turn-on Rise Time	$t_r$		-	11	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	20	-	nS
Turn-Off Fall Time	$t_f$		-	12	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=160V, I_D=4.5A,$ $V_{GS}=10V$	-	16	-	nC
Gate-Source Charge	$Q_{gs}$		-	3.4	-	nC
Gate-Drain Charge	$Q_{gd}$		-	5.1	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_S=8A$	-	-	1.2	V
Diode Forward Current	$I_S$		-	-	8	A

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics (Curves)

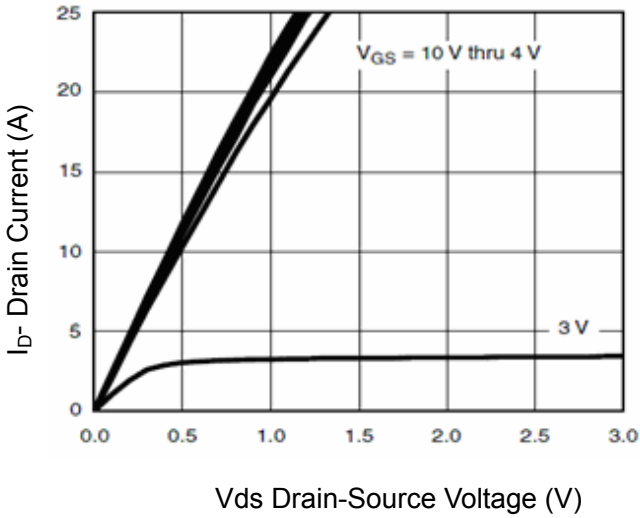


Figure 1 Output Characteristics

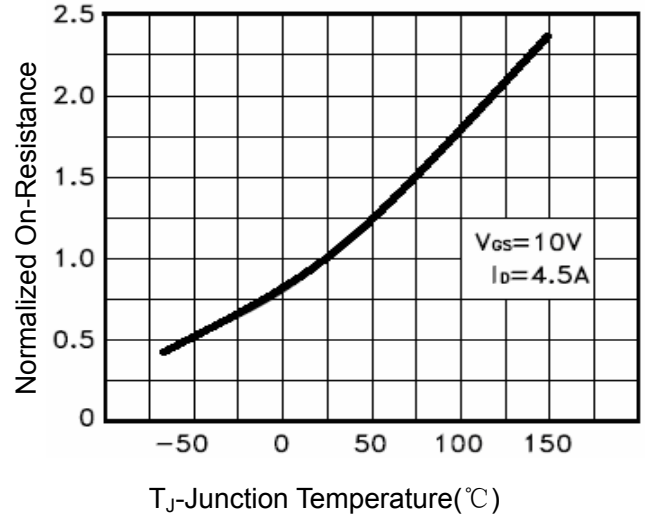


Figure 4 Rdson-Junction Temperature

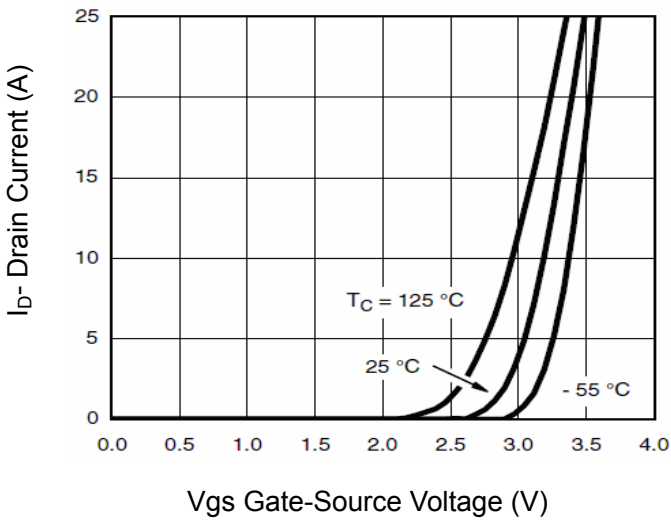


Figure 2 Transfer Characteristics

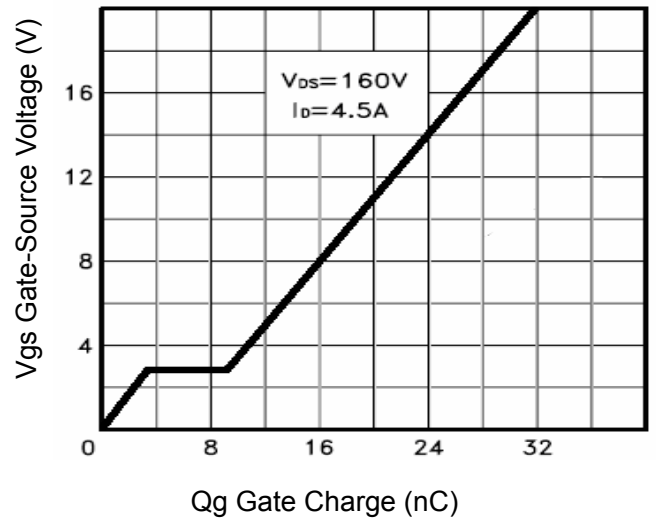


Figure 5 Gate Charge

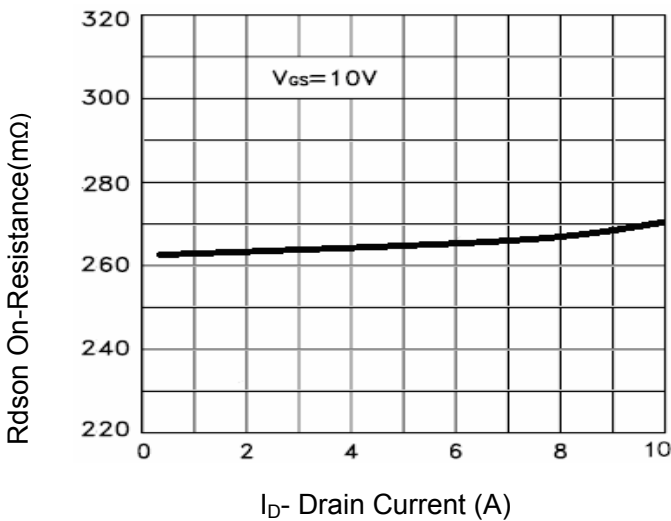


Figure 3 Rdson- Drain Current

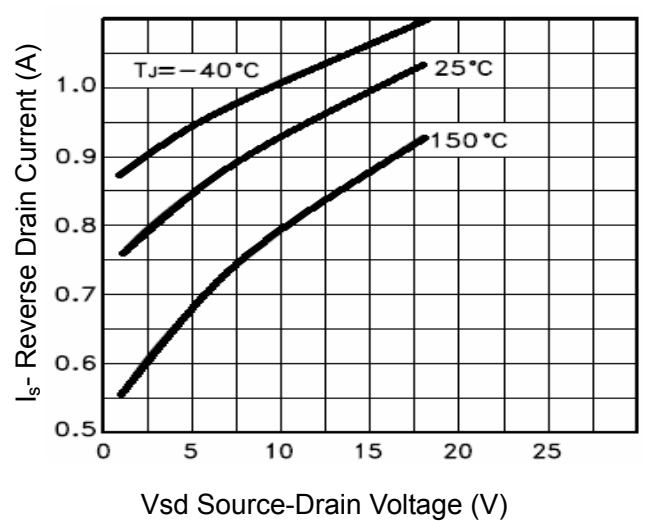


Figure 6 Source- Drain Diode Forward

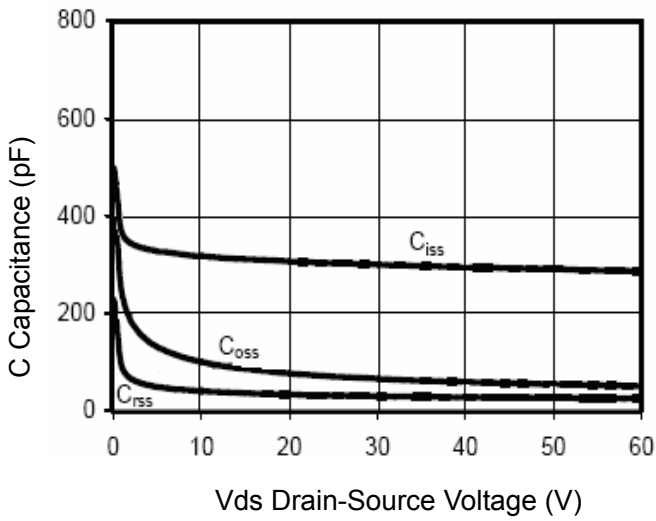


Figure 7 Capacitance vs Vds

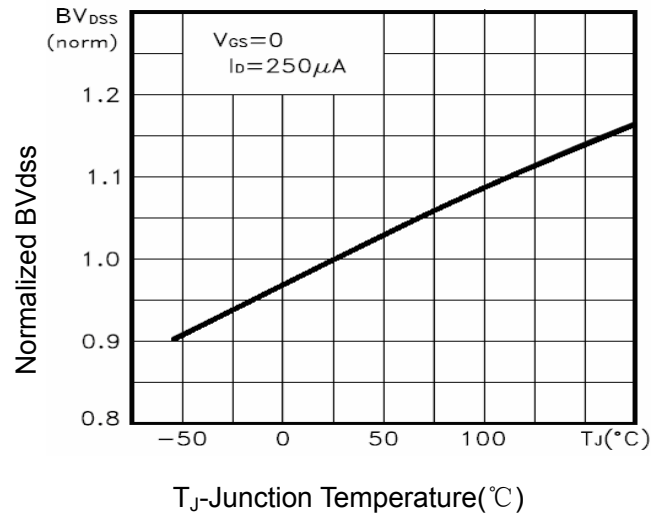


Figure 9  $BV_{DSS}$  vs Junction Temperature

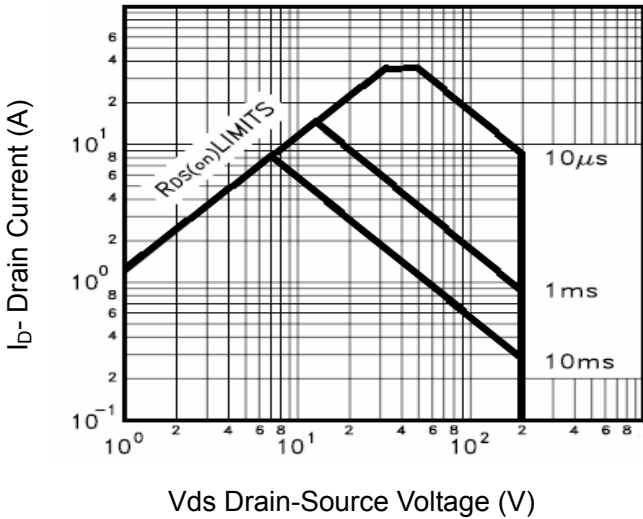


Figure 8 Safe Operation Area

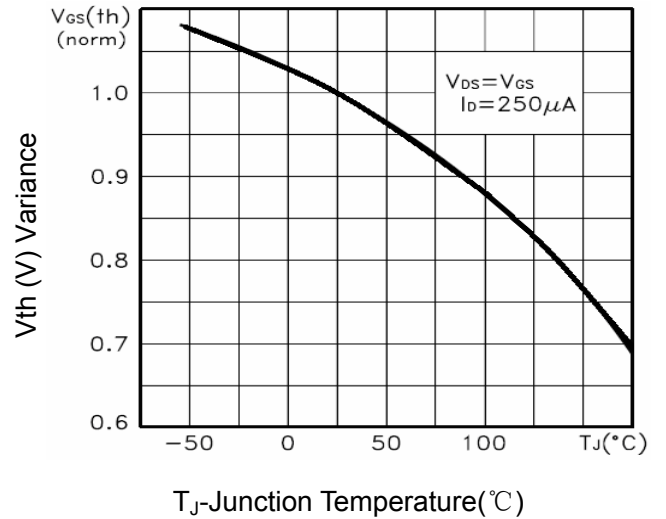


Figure 10  $V_{GS(th)}$  vs Junction Temperature

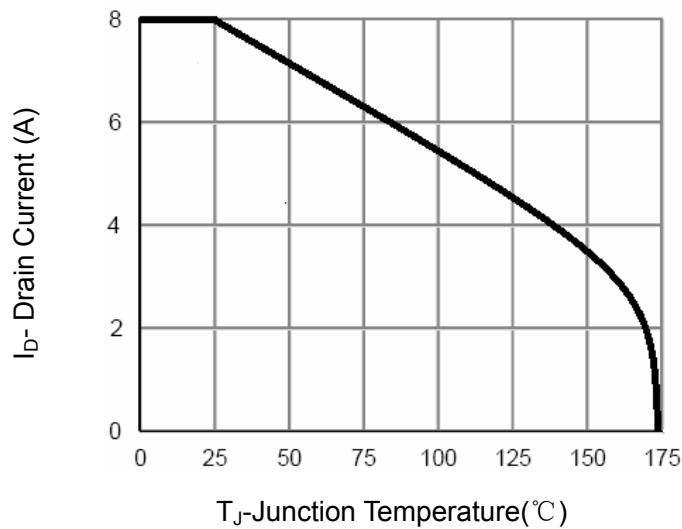


Figure 11 Current De-rating

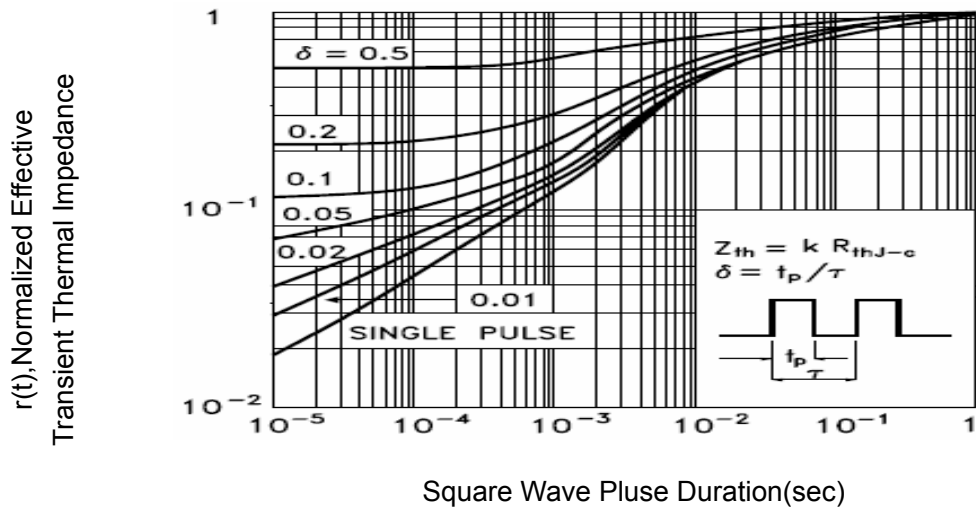


Figure 12 Normalized Maximum Transient Thermal Impedance